

Session Program

16-18 Nov 2009

15th RD50 Workshop

Defect Characterization

CERN, TE Auditorium

Monday 16 November

14:45

Defect Characterization

Session | **Location:** CERN, TE Auditorium

14:45–15:05

The comparison of the defect generation during the proton irradiation in situ and afterwards in silicon

Speaker

Prof. Juozas Vaitkus

15:05–15:25

INTERSTITIAL DEFECT REACTIONS IN P-TYPE SILICON IRRADIATED AT DIFFERENT TEMPERATURES

Speaker

Dr Leonid Makarenko

15:25–15:55

coffee break

15:55–16:15

The deep levels in the irradiated Si (WODEAN samples)

Speaker

Prof. Juozas Vaitkus

16:15–16:35

Microscopic Study of Proton Irradiated Epitaxial Detectors

Speaker

Volodymyr Khomenkov

16:35–16:55

Generation of a shallow donor after 6, 15 and 900 MeV electron irradiation

Speaker

alexandra junkes

16:55–17:15

TSC studies on n- and p-type MCZ Si pad detectors irradiated with neutrons up to 10^{16} n/cm²

Speaker

Monica Scaringella

17:15–17:35

Discussion: Wodean & Defect Characterization

17:35